

1SS390

SILICON EPITAXIAL PLANAR DIODE

FEATURES :

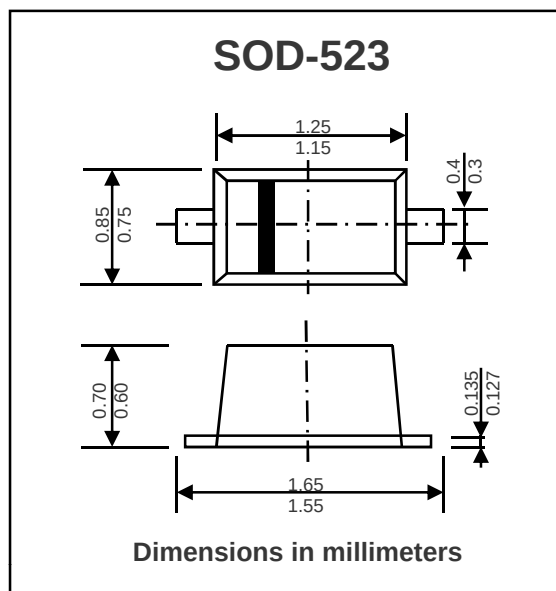
- * Extremely small surface mounting type
- * High reliability

Applications

- * High frequency switching

MECHANICAL DATA :

- * Case : SOD-523 plastic Case
- * Marking Code : " K "



Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Reverse Voltage	V_R	35	V
Maximum Average Forward Current	I_F	100	mA
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-55 to + 125	°C

Electrical Characteristics (Ta = 25 °C)

Parameter	Symbol	Test Condition	Max.	Unit
Forward Voltage	V_F	$I_F = 10 \text{ mA}$	1.0	V
Reverse Current	I_R	$V_R = 25 \text{ V}$	10	μA
Total Capacitance	C_T	at $V_R = 6 \text{ V}$, $f = 1 \text{ MHz}$	1.2	pF
Forward Operation Resistance	r_f	at $I_F = 2 \text{ mA}$, $f = 100 \text{ MHz}$	0.9	Ω

RATING AND CHARACTERISTIC CURVES (1SS390)

FIG.1 - FORWARD CHARACTERISTICS

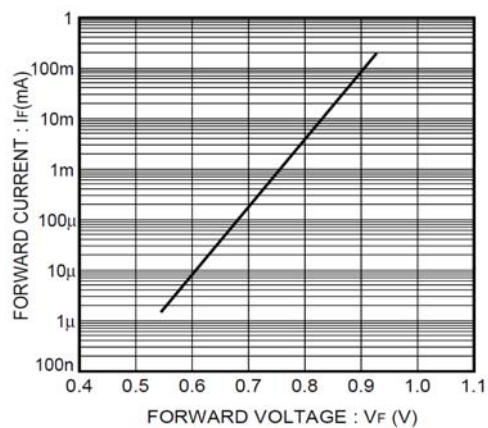


FIG.2 - REVERSE CHARACTERISTICS

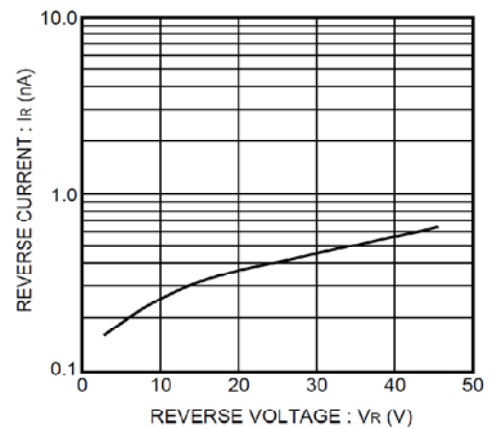


FIG.3 - CAPACITANCE VS. TERMINALS CHARACTERISTICS

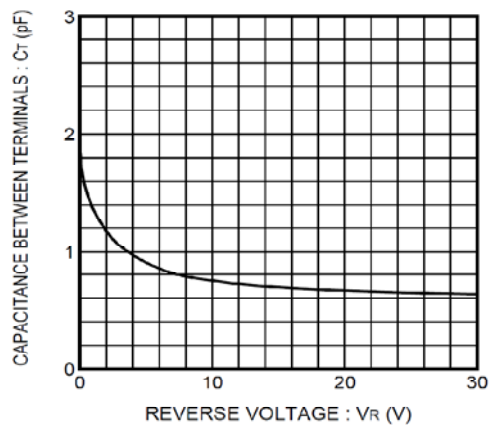


FIG.4 - FORWARD OPERATING RESISTANCE CHARACTERISTICS

